



SPA-LEED pattern measured during Homoepitaxial Growth of Si on Si(111)

in H₂ at:
 $p = 5 \times 10^{-7}$ mbar, $T = 520$ °C, $E = 75.6$ eV.
 (M. Horn-von Hoegen and A. Golla, Surf. Sci. Lett. 337 (1995) L777-82)

Cover picture of Omicron Newsletter I/97

